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| Form 1449*  | Atty. Docket No.: 303.684US3 | Serial No. Unknown |
| INFORMATION DISCLOSURE STATEMENT<br>BY APPLICANT<br>(Use several sheets if necessary) | Applicant: Leonard Forbes    |                    |
|   | Filing Date: Herewith        | Group: Unknown     |

10/04/06  
10/09/02

## U.S. PATENT DOCUMENTS

| **Examiner<br>Initial | Document Number | Date       | Name                 | Class | Subclass | Filing Date<br>If Appropriate |
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| **Examiner<br>Initial | Document Number | Date | Country | Class | Subclass | Translation<br>Yes   No |
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\*Substitute Disclosure Statement Form (PTO-1449)

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|   |                              |  |
|---|------------------------------|--|
| Form 1449*  | Atty. Docket No.: 303.684US3 | Serial No. <del>Unknown</del> 10/043/065 |
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